



Fig. (1a) GPC against the TDMASn pulse time for PE - ALD process at 80 °C and 180 °C **Fig. (1b)** GPC against the H₂S plasma pulse time for PE - ALD process at 80 °C and 180 °C. **Fig. (2)** XRD of the thin films deposited by PE-ALD and thermal ALD process at 80 °C and 180 °C. **Fig. (3)** Top view SEM images for SnS₂ thin films deposited by **(3a)** Thermal ALD process at 80 °C **(3b)** PE - ALD process at 80 °C **(3c)** PE - ALD process at 180 °C. **Fig. (4)** Tauc plot of the SnS₂ thin films deposited by PE - ALD process at 80 °C and 180 °C, and thermal ALD process at 80 °C. **Fig. (5)** Cyclic performance of all as deposited SnS₂ electrodes by PE - ALD process at 80 °C and 180 °C, and thermal ALD process at 80 °C.